

GATE CONTROLLED DEVICE - Insulated Gate Bi-polar Transistor - Capsule Type

Old Part Number	PDF Data Sheet Available	New Part Number	V _{CES} (V)	V _{GES} (V)	I _C (Note 2) (A)	I _{CRM} (Note 2) (A)	I _F (A)	I _{FRM} (A)	P _{MAX} (W)	T _J (Note 3) (°C)	T _{stg} (°C)	Rth(j-hs) (IGBT)			Rth(j-hs) (Diode)			Wt (Typ) (g)	Mounting Force (kN)	Outline No. (Note 4)
												Double (K/kW)	Collector (K/kW)	Emitter (K/kW)	Double (K/kW)	Cathode (K/kW)	Anode (K/kW)			
WTC40AAC18	Y	T0400NA18A	1800	+/- 20	400	800	400	800	1800	-60 to +150	-60 to +150	55	90	140	84	138	218	50	8.0 - 12.0	n/a
WTC140AAC18	Y	T1400TA18A	1800	+/- 20	1400	2800	1400	2800	6600	-60 to +150	-60 to +150	15	25	39	35	52	104	120	20.0 - 30.0	n/a

The information contained herein is confidential and is protected by Copyright. The information may not be used or disclosed except with the written permission of and in the manner permitted by the proprietors Westcode Semiconductors Limited. In the interest of product improvement, Westcode reserves the right to change specifications at any time without prior notice.

Note 1 Unless otherwise indicated, T_J = 125°C

Note 2 T_C = 90°C

Note 3 For operation below -40°C or above +125°C, please contact the Factory.

Note 4 Please refer to data sheets for outline drawings